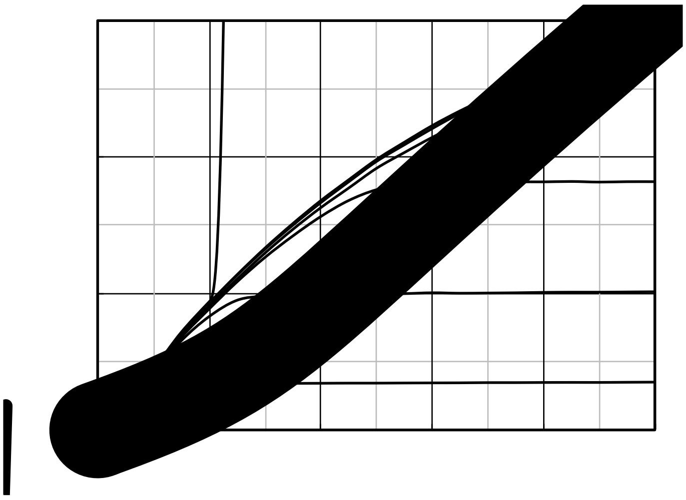
N-Channel Enhancement Mode Field Effect Transisreltr

Electrical Characteristics (T_J=25 unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Static Parameter						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}= 0V, I_D	900	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=900V, V_{GS}=0V	-	-	1	
		V_{DS}=900V, V_{GS}=0V, Tj=150	-	-	100	
Gate-Body Leakage Current	I_{GSS}	V_{GS}= ±30V, V_{DS}=0V	-	-	±100	nA

■Typical Electrical and Thermal Characteristics Diagrams



[redacted]

Figure 1. Output Characteristics

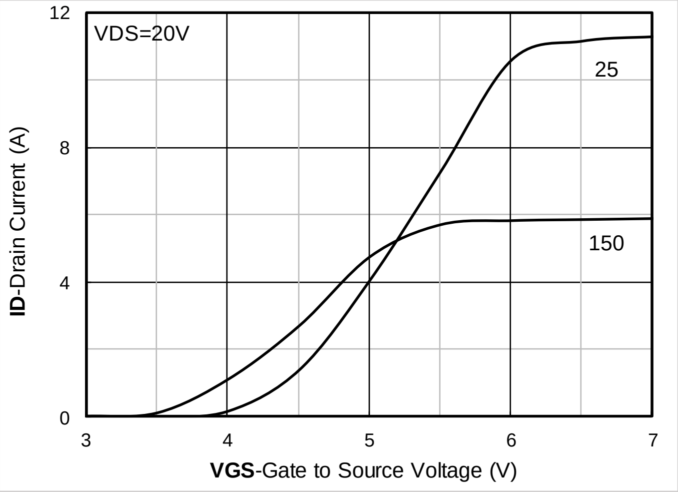


Figure 2. Transfer Characteristics

Figure 3. Capacitance Characteristics

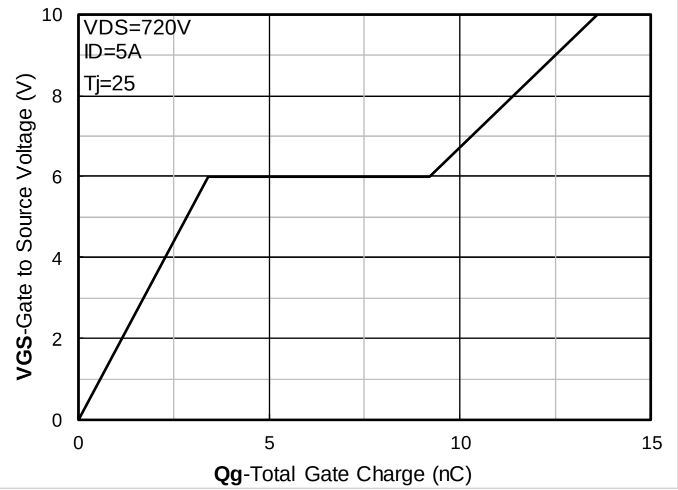


Figure 4. Gate Charge

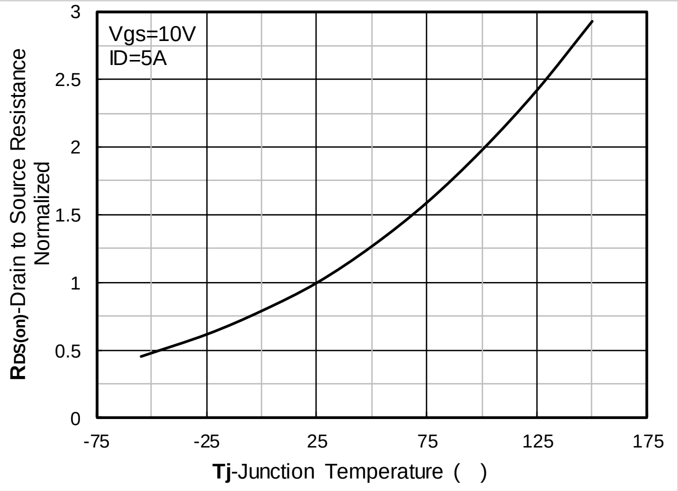


Figure 5. On-Resistance vs Gate to Source Voltage

Figure 6. Normalized On-Resistance

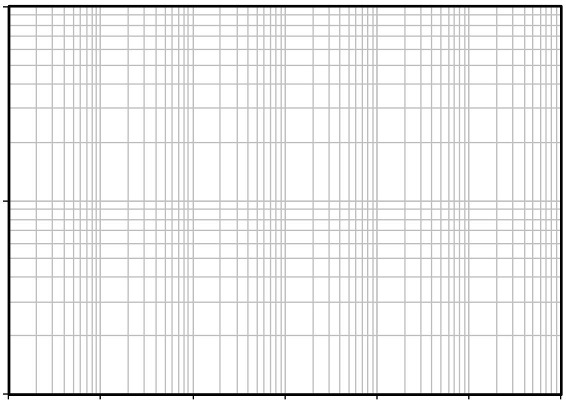


Figure 13. Maximum Transient Thermal Impedance

Figure 14. Safe Operation Area

Test Circuits & Waveforms

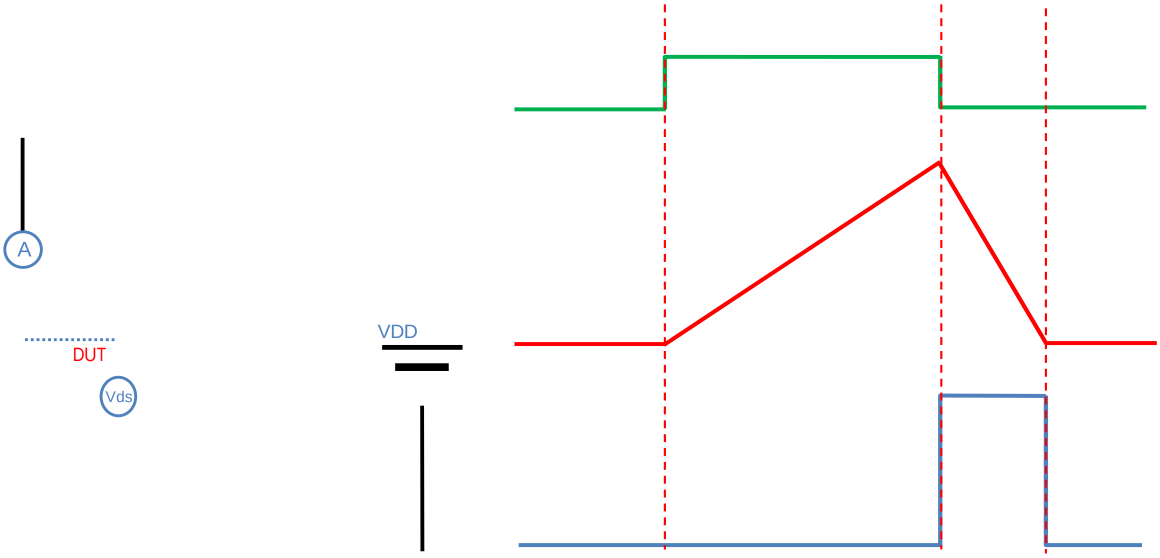


Figure A. Unclamped Inductive Switching (UIS) Test Circuit & Waveform

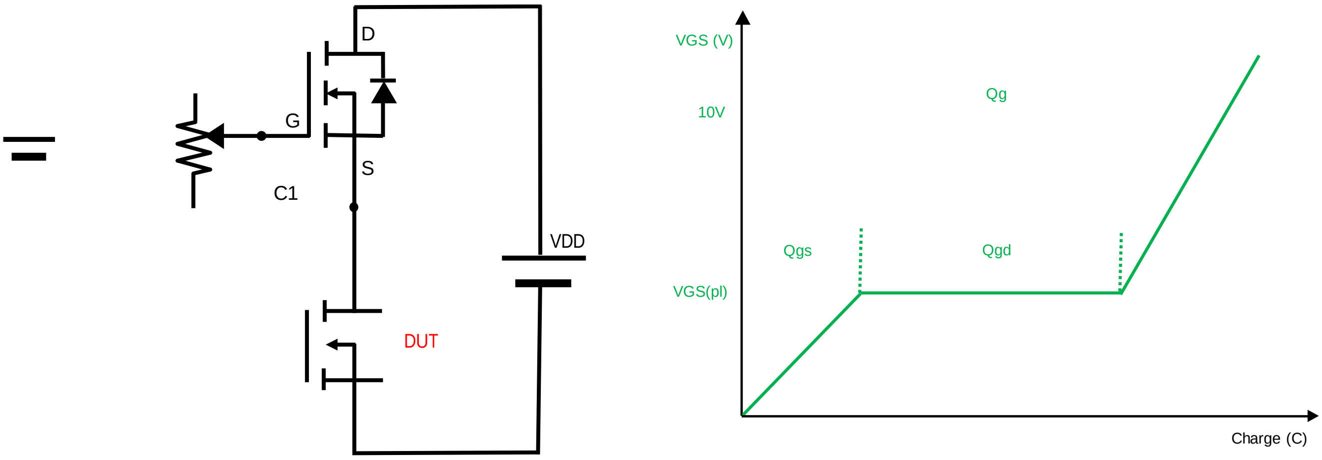


Figure B. Gate Charge Test Circuit & Waveform

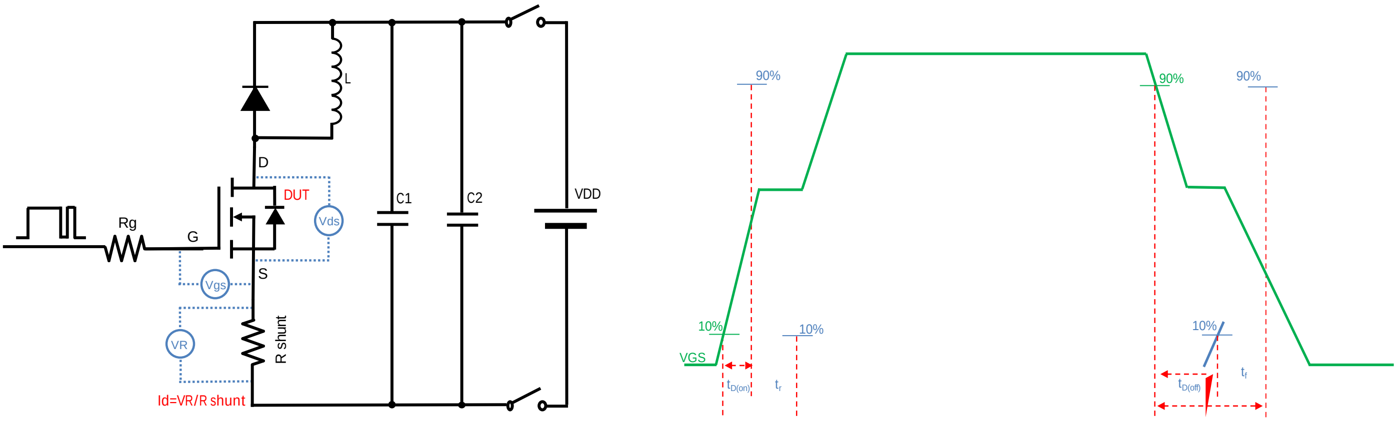


Figure C. Resistive Switching Test Circuit & Waveform

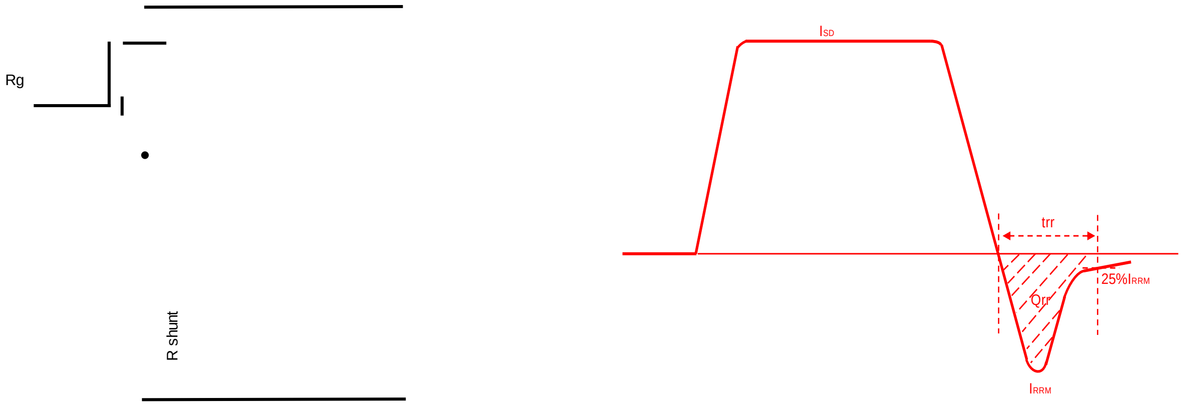


Figure D. Diode Recovery Test Circuit & Waveform

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